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Understanding Embedded - Microprocessors

Embedded microprocessors are specialized computing chips designed to perform specific tasks within an embedded system. Unlike general-purpose microprocessors found in personal computers, embedded microprocessors are tailored for dedicated functions within larger systems, offering optimized performance, efficiency, and reliability. These microprocessors are integral to the operation of countless electronic devices, providing the computational power necessary for controlling processes, handling data, and managing communications.

Applications of Embedded - Microprocessors

Embedded microprocessors are utilized across a broad spectrum of applications, making them indispensable in

Details	
Product Status	Active
Core Processor	PowerPC e500
Number of Cores/Bus Width	1 Core, 32-Bit
Speed	1.0GHz
Co-Processors/DSP	Signal Processing; SPE
RAM Controllers	DDR, DDR2, SDRAM
Graphics Acceleration	No
Display & Interface Controllers	-
Ethernet	10/100/1000Mbps (2)
SATA	-
USB	-
Voltage - I/O	1.8V, 2.5V, 3.3V
Operating Temperature	0°C ~ 105°C (TA)
Security Features	-
Package / Case	783-BBGA, FCBGA
Supplier Device Package	783-FCPBGA (29x29)
Purchase URL	https://www.e-xfl.com/pro/item?MUrl=&PartUrl=mpc8544vtaqga

- Double-precision floating-point APU. Provides an instruction set for double-precision (64-bit) floating-point instructions that use the 64-bit GPRs.
- 36-bit real addressing
- Embedded vector and scalar single-precision floating-point APUs. Provide an instruction set for single-precision (32-bit) floating-point instructions.
- Memory management unit (MMU). Especially designed for embedded applications. Supports 4-Kbyte–4-Gbyte page sizes.
- Enhanced hardware and software debug support
- Performance monitor facility that is similar to, but separate from, the device performance monitor

The e500 defines features that are not implemented on this device. It also generally defines some features that this device implements more specifically. An understanding of these differences can be critical to ensure proper operations.

- 256-Kbyte L2 cache/SRAM
  - Flexible configuration
  - Full ECC support on 64-bit boundary in both cache and SRAM modes
  - Cache mode supports instruction caching, data caching, or both.
  - External masters can force data to be allocated into the cache through programmed memory ranges or special transaction types (stashing).
    - 1, 2, or 4 ways can be configured for stashing only.
  - Eight-way set-associative cache organization (32-byte cache lines)
  - Supports locking entire cache or selected lines. Individual line locks are set and cleared through Book E instructions or by externally mastered transactions.
  - Global locking and flash clearing done through writes to L2 configuration registers
  - Instruction and data locks can be flash cleared separately.
  - SRAM features include the following:
    - I/O devices access SRAM regions by marking transactions as snoopable (global).
    - Regions can reside at any aligned location in the memory map.
    - Byte-accessible ECC is protected using read-modify-write transaction accesses for smaller-than-cache-line accesses.
- Address translation and mapping unit (ATMU)
  - Eight local access windows define mapping within local 36-bit address space.
  - Inbound and outbound ATMUs map to larger external address spaces.
    - Three inbound windows plus a configuration window on PCI and PCI Express
    - Four outbound windows plus default translation for PCI and PCI Express
- DDR/DDR2 memory controller
  - Programmable timing supporting DDR and DDR2 SDRAM
  - 64-bit data interface

  - Four banks of memory supported, each up to 4 Gbytes, to a maximum of 16 Gbytes
  - DRAM chip configurations from 64 Mbits to 4 Gbits with x8/x16 data ports
  - Full ECC support
  - Page mode support
    - Up to 16 simultaneous open pages for DDR
    - Up to 32 simultaneous open pages for DDR2
  - Contiguous or discontiguous memory mapping
  - Sleep mode support for self-refresh SDRAM
  - On-die termination support when using DDR2
  - Supports auto refreshing
  - On-the-fly power management using CKE signal
  - Registered DIMM support
  - Fast memory access via JTAG port
  - 2.5-V SSTL_2 compatible I/O (1.8-V SSTL_1.8 for DDR2)
- Programmable interrupt controller (PIC)
  - Programming model is compliant with the OpenPIC architecture.
  - Supports 16 programmable interrupt and processor task priority levels
  - Supports 12 discrete external interrupts
  - Supports 4 message interrupts with 32-bit messages
  - Supports connection of an external interrupt controller such as the 8259 programmable interrupt controller
  - Four global high resolution timers/counters that can generate interrupts
  - Supports a variety of other internal interrupt sources
  - Supports fully nested interrupt delivery
  - Interrupts can be routed to external pin for external processing.
  - Interrupts can be routed to the e500 core's standard or critical interrupt inputs.
  - Interrupt summary registers allow fast identification of interrupt source.
- Integrated security engine (SEC) optimized to process all the algorithms associated with IPSec, IKE, WTLS/WAP, SSL/TLS, and 3GPP
  - Four crypto-channels, each supporting multi-command descriptor chains
    - Dynamic assignment of crypto-execution units via an integrated controller
    - Buffer size of 256 bytes for each execution unit, with flow control for large data sizes
  - PKEU—public key execution unit
    - RSA and Diffie-Hellman; programmable field size up to 2048 bits
    - Elliptic curve cryptography with F_2m and F(p) modes and programmable field size up to 511 bits
  - DEU—Data Encryption Standard execution unit
    - DES, 3DES

4.2 Real-Time Clock Timing

The RTC input is sampled by the platform clock (CCB clock). The output of the sampling latch is then used as an input to the counters of the PIC and the TimeBase unit of the e500. There is no jitter specification. The minimum pulse width of the RTC signal should be greater than 2 × the period of the CCB clock. That is, minimum clock high time is $2 \times t_{CCB}$, and minimum clock low time is $2 \times t_{CCB}$. There is no minimum RTC frequency; RTC may be grounded if not needed.

4.3 eTSEC Gigabit Reference Clock Timing

Table 7 provides the eTSEC gigabit reference clocks (EC_GTX_CLK125) AC timing specifications for the MPC8544E.

Table 7. EC_GTX_CLK125 AC Timing Specifications

Parameter/Condition	Symbol	Min	Typ	Max	Unit	Notes
EC_GTX_CLK125 frequency	f_{G125}	—	125	—	MHz	—
EC_GTX_CLK125 cycle time	t_{G125}	—	8	—	ns	—
EC_GTX_CLK rise and fall time LV_{DD}, TV_{DD} = 2.5 V LV_{DD}, TV_{DD} = 3.3 V	t_{G125R}/t_{G125F}	—	—	 0.75 1.0	ns	1
EC_GTX_CLK125 duty cycle GMII, TBI 1000Base-T for RGMII, RTBI	t_{G125H}/t_{G125}	 45 47	—	 55 53	%	2

Notes:

1. Rise and fall times for EC_GTX_CLK125 are measured from 0.5 and 2.0 V for L/TV_{DD} = 2.5 V, and from 0.6 and 2.7 V for L/TVDD = 3.3 V.
2. EC_GTX_CLK125 is used to generate the GTX clock for the eTSEC transmitter with 2% degradation. EC_GTX_CLK125 duty cycle can be loosened from 47%/53% as long as the PHY device can tolerate the duty cycle generated by the eTSEC GTX_CLK. See Section 8.7.4, “RGMII and RTBI AC Timing Specifications,” for duty cycle for 10Base-T and 100Base-T reference clock.

4.4 Platform to FIFO Restrictions

Please note the following FIFO maximum speed restrictions based on platform speed.

For FIFO GMII mode:

FIFO TX/RX clock frequency ≤ platform clock frequency ÷ 4.2

For example, if the platform frequency is 533 MHz, the FIFO Tx/Rx clock frequency should be no more than 127 MHz.

For FIFO encoded mode:

FIFO TX/RX clock frequency ≤ platform clock frequency ÷ 3.2

For example, if the platform frequency is 533 MHz, the FIFO Tx/Rx clock frequency should be no more than 167 MHz.

Table 18. DDR SDRAM Output AC Timing Specifications (continued)

At recommended operating conditions.

Parameter	Symbol[1]	Min	Max	Unit	Notes
MDQS postamble	t_{DDKHME}	0.4 x tMCK	0.6 x tMCK	ns	6

Notes:

1. The symbols used for timing specifications follow the pattern of $t_{\text{(first two letters of functional block)(signal)(state)(reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. Output hold time can be read as DDR timing (DD) from the rising or falling edge of the reference clock (KH or KL) until the output went invalid (AX or DX). For example, t_{DDKHAS} symbolizes DDR timing (DD) for the time t_{MCK} memory clock reference (K) goes from the high (H) state until outputs (A) are setup (S) or output valid time. Also, t_{DDKLDX} symbolizes DDR timing (DD) for the time t_{MCK} memory clock reference (K) goes low (L) until data outputs (D) are invalid (X) or data output hold time.
2. All MCK/$\overline{\text{MCK}}$ referenced measurements are made from the crossing of the two signals ±0.1 V.
3. ADDR/CMD includes all DDR SDRAM output signals except MCK/$\overline{\text{MCK}}$, $\overline{\text{MCS}}$, and MDQ/MECC/MDM/MDQS.
4. Note that t_{DDKHMH} follows the symbol conventions described in note 1. For example, t_{DDKHMH} describes the DDR timing (DD) from the rising edge of the MCK[n] clock (KH) until the MDQS signal is valid (MH). t_{DDKHMH} can be modified through control of the DQSS override bits in the TIMING_CFG_2 register. This will typically be set to the same delay as the clock adjust in the CLK_CNTL register. The timing parameters listed in the table assume that these two parameters have been set to the same adjustment value. See the *MPC8544E PowerQUICC III Integrated Communications Processor Reference Manual,* for a description and understanding of the timing modifications enabled by use of these bits.
5. Determined by maximum possible skew between a data strobe (MDQS) and any corresponding bit of data (MDQ), ECC (MECC), or data mask (MDM). The data strobe should be centered inside of the data eye at the pins of the microprocessor.
6. All outputs are referenced to the rising edge of MCK[n] at the pins of the microprocessor. Note that t_{DDKHMP} follows the symbol conventions described in note 1.
7. Maximum DDR1 frequency is 400 MHz.

NOTE

For the ADDR/CMD setup and hold specifications in Table 18, it is assumed that the clock control register is set to adjust the memory clocks by ½ applied cycle.

Figure 4 shows the DDR SDRAM output timing for the MCK to MDQS skew measurement (t_{DDKHMH}).

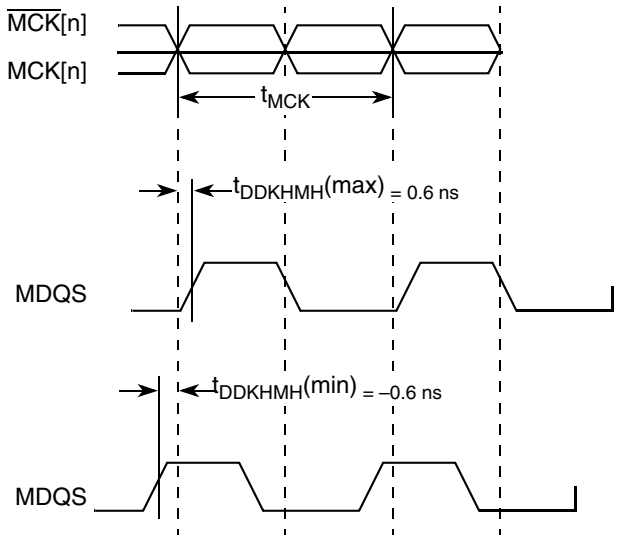

Figure 4. Timing Diagram for t_{DDKHMH}

Figure 5 shows the DDR SDRAM output timing diagram.

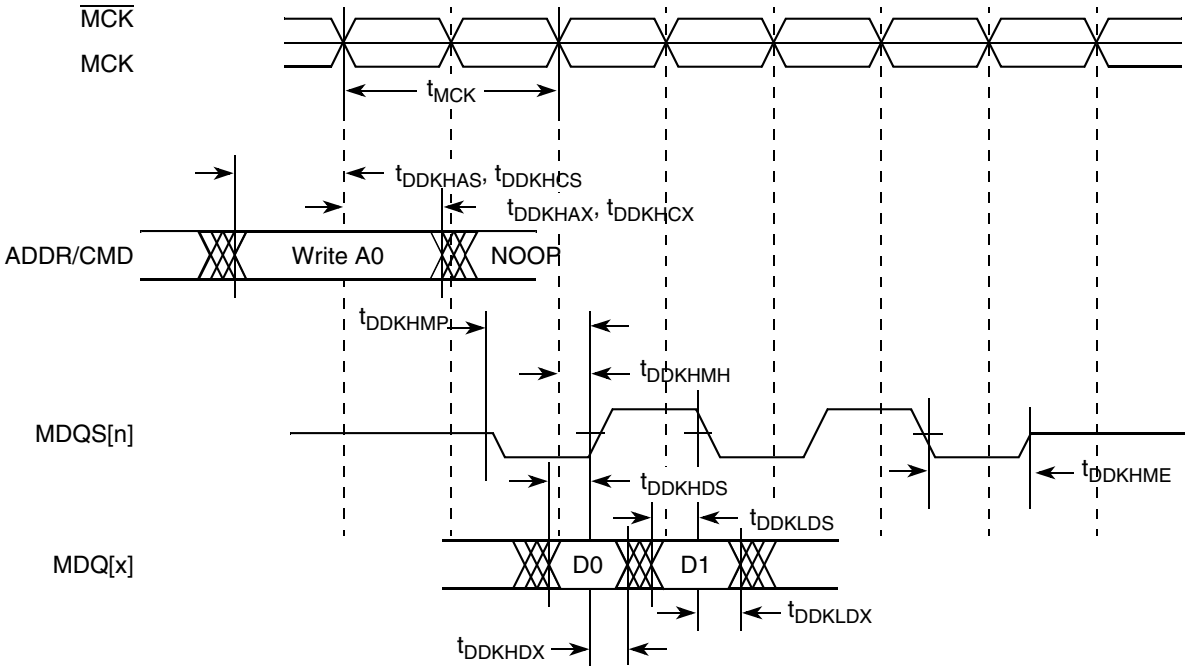

Figure 5. DDR and DDR2 SDRAM Output Timing Diagram

Figure 6 provides the AC test load for the DDR bus.

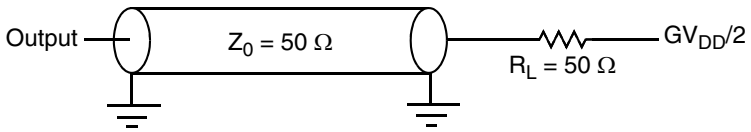

Figure 6. DDR AC Test Load

7 DUART

This section describes the DC and AC electrical specifications for the DUART interface of the MPC8544E.

7.1 DUART DC Electrical Characteristics

Table 19 provides the DC electrical characteristics for the DUART interface.

Table 19. DUART DC Electrical Characteristics

Parameter	Symbol	Min	Max	Unit	Notes
High-level input voltage	V_{IH}	2	OV_{DD} + 0.3	V	—
Low-level input voltage	V_{IL}	–0.3	0.8	V	—
Input current (V_{IN} = 0 V or V_{IN} = V_{DD})	I_{IN}	—	±5	μA	1
High-level output voltage (OV_{DD} = min, I_{OH} = –2 mA)	V_{OH}	2.4	—	V	—

Characteristics.”

8.2 eTSEC DC Electrical Characteristics

All GMII, MII, TBI, RGMII, RTBI, RMII, and FIFO drivers and receivers comply with the DC parametric attributes specified in Table 21 and Table 22. The potential applied to the input of a GMII, MII, TBI, RTBI, RMII, and FIFO receiver may exceed the potential of the receiver’s power supply (that is, a GMII driver powered from a 3.6-V supply driving V_{OH} into a GMII receiver powered from a 2.5-V supply). Tolerance for dissimilar GMII driver and receiver supply potentials is implicit in these specifications. The RGMII and RTBI signals are based on a 2.5-V CMOS interface voltage as defined by JEDEC EIA/JESD8-5.

Table 21. GMII, MII, TBI, RMII and FIFO DC Electrical Characteristics

Parameter	Symbol	Min	Max	Unit	Notes
Supply voltage 3.3 V	LV_{DD} TV_{DD}	3.135	3.465	V	1, 2
Output high voltage (LV_{DD}/TV_{DD} = Min, I_{OH} = –4.0 mA)	V_{OH}	2.4	—	V	—
Output low voltage (LV_{DD}/TV_{DD} = Min, I_{OL} = 4.0 mA)	V_{OL}	—	0.5	V	—
Input high voltage	V_{IH}	1.95	—	V	—
Input low voltage	V_{IL}	—	0.90	V	—
Input high current (V_{IN} = LV_{DD}, V_{IN} = TV_{DD})	I_{IH}	—	40	μA	1, 2, 3
Input low current (V_{IN} = GND)	I_{IL}	–600	—	μA	3

Notes:
1. LV_{DD} supports eTSEC1.
2. TV_{DD} supports eTSEC3.
3. The symbol V_{IN}, in this case, represents the LV_{IN} and TV_{IN} symbols referenced in Table 1 and Table 2.

Table 22. GMII, MII, RMII, RGMII, RTBI, TBI, and FIFO DC Electrical Characteristics

Parameters	Symbol	Min	Max	Unit	Notes
Supply voltage 2.5 V	LV_{DD}/TV_{DD}	2.375	2.625	V	1, 2
Output high voltage (LV_{DD}/TV_{DD} = Min, I_{OH} = –1.0 mA)	V_{OH}	2.0	—	V	—
Output low voltage (LV_{DD}/TV_{DD} = Min, I_{OL} = 1.0 mA)	V_{OL}	—	0.4	V	—
Input high voltage	V_{IH}	1.70	—	V	—
Input low voltage	V_{IL}	—	0.7	V	—
Input current (V_{IN} = 0, V_{IN} = LV_{DD}, V_{IN} = TV_{DD})	I_{IN}	—	±15	μA	1, 2, 3

Notes:
1. LV_{DD} supports eTSEC1.
2. TV_{DD} supports eTSEC3.
3. The symbol V_{IN}, in this case, represents the LV_{IN} and TV_{IN} symbols referenced in Table 1 and Table 2.

A summary of the single-clock TBI mode AC specifications for receive appears in Table 36.

Table 36. TBI Single-Clock Mode Receive AC Timing Specification

Parameter/Condition	Symbol	Min	Typ	Max	Unit	Notes
RX_CLK clock period	t_{TRR}	7.5	8.0	8.5	ns	—
RX_CLK duty cycle	t_{TRRH}	40	50	60	%	—
RX_CLK peak-to-peak jitter	t_{TRRJ}	—	—	250	ps	—
Rise time RX_CLK (20%–80%)	t_{TRRR}	—	—	1.0	ns	—
Fall time RX_CLK (80%–20%)	t_{TRRF}	—	—	1.0	ns	—
RCG[9:0] setup time to RX_CLK rising edge	t_{TRRDV}	2.0	—	—	ns	—
RCG[9:0] hold time to RX_CLK rising edge	t_{TRRDX}	1.0	—	—	ns	—

A timing diagram for TBI receive appears in Figure 21.

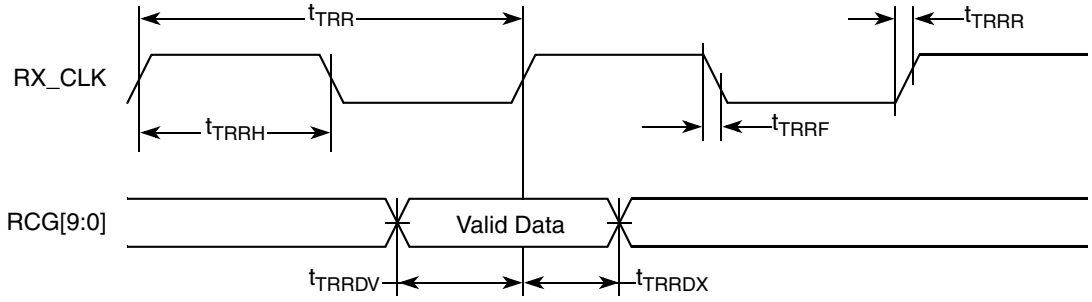

Figure 21. TBI Single-Clock Mode Receive AC Timing Diagram

8.7.4 RGMII and RTBI AC Timing Specifications

Table 37 presents the RGMII and RTBI AC timing specifications.

Table 37. RGMII and RTBI AC Timing Specifications

At recommended operating conditions with L/TV_{DD} of 2.5 V ± 5%.

Parameter/Condition	Symbol[1]	Min	Typ	Max	Unit	Notes
Data to clock output skew (at transmitter)	t_{SKRGT_TX}	–500	0	500	ps	5
Data to clock input skew (at receiver)	t_{SKRGT_RX}	1.0	—	2.8	ns	2
Clock period duration	t_{RGT}	7.2	8.0	8.8	ns	3
Duty cycle for 10BASE-T and 100BASE-TX	t_{RGTH}/t_{RGT}	40	50	60	%	3, 4
Rise time (20%–80%)	t_{RGTR}	—	—	0.75	ns	—

Table 45. Local Bus General Timing Parameters (BV_{DD} = 3.3 V)—PLL Enabled (continued)

Parameter	Symbol[1]	Min	Max	Unit	Notes
Local bus clock to output high impedance for LAD/LDP	$t_{LBKHOZ2}$	—	2.5	ns	5

Notes:
1. The symbols used for timing specifications follow the pattern of $t_{\text{(first two letters of functional block)(signal)(state)(reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, $t_{LBIXKH1}$ symbolizes local bus timing (LB) for the input (I) to go invalid (X) with respect to the time the t_{LBK} clock reference (K) goes high (H), in this case for clock one (1). Also, t_{LBKHOX} symbolizes local bus timing (LB) for the t_{LBK} clock reference (K) to go high (H), with respect to the output (O) going invalid (X) or output hold time.
2. All timings are in reference to LSYNC_IN for PLL enabled and internal local bus clock for PLL bypass mode.
3. All signals are measured from $BV_{DD}/2$ of the rising edge of LSYNC_IN for PLL enabled or internal local bus clock for PLL bypass mode to $0.4 \times BV_{DD}$ of the signal in question for 3.3-V signaling levels.
4. Input timings are measured at the pin.
5. For purposes of active/float timing measurements, the Hi-Z or off state is defined to be when the total current delivered through the component pin is less than or equal to the leakage current specification.
6. t_{LBOTOT} is a measurement of the minimum time between the negation of LALE and any change in LAD. t_{LBOTOT} is programmed with the LBCR[AHD] parameter.
7. Maximum possible clock skew between a clock LCLK[m] and a relative clock LCLK[n]. Skew measured between complementary signals at $BV_{DD}/2$.

Table 46 describes the general timing parameters of the local bus interface at BV_{DD} = 2.5 V.

Table 46. Local Bus General Timing Parameters (BV_{DD} = 2.5 V)—PLL Enabled

Parameter	Symbol[1]	Min	Max	Unit	Notes
Local bus cycle time	t_{LBK}	7.5	12	ns	2
Local bus duty cycle	t_{LBKH}/t_{LBK}	43	57	%	—
LCLK[n] skew to LCLK[m] or LSYNC_OUT	$t_{LBKSKEW}$	—	150	ps	7
Input setup to local bus clock (except LUPWAIT)	$t_{LBIVKH1}$	2.4	—	ns	3, 4
LUPWAIT input setup to local bus clock	$t_{LBIVKH2}$	1.8	—	ns	3, 4
Input hold from local bus clock (except LUPWAIT)	$t_{LBIXKH1}$	1.1	—	ns	3, 4
LUPWAIT input hold from local bus clock	$t_{LBIXKH2}$	1.1	—	ns	3, 4
LALE output transition to LAD/LDP output transition (LATCH setup and hold time)	t_{LBOTOT}	1.5	—	ns	6
Local bus clock to output valid (except LAD/LDP and LALE)	$t_{LBKHOV1}$	—	2.8	ns	—
Local bus clock to data valid for LAD/LDP	$t_{LBKHOV2}$	—	2.8	ns	3
Local bus clock to address valid for LAD	$t_{LBKHOV3}$	—	2.8	ns	3
Local bus clock to LALE assertion	$t_{LBKHOV4}$	—	2.8	ns	3
Output hold from local bus clock (except LAD/LDP and LALE)	$t_{LBKHOX1}$	0.8	—	ns	3
Output hold from local bus clock for LAD/LDP	$t_{LBKHOX2}$	0.8	—	ns	3
Local bus clock to output high Impedance (except LAD/LDP and LALE)	$t_{LBKHOZ1}$	—	2.6	ns	5

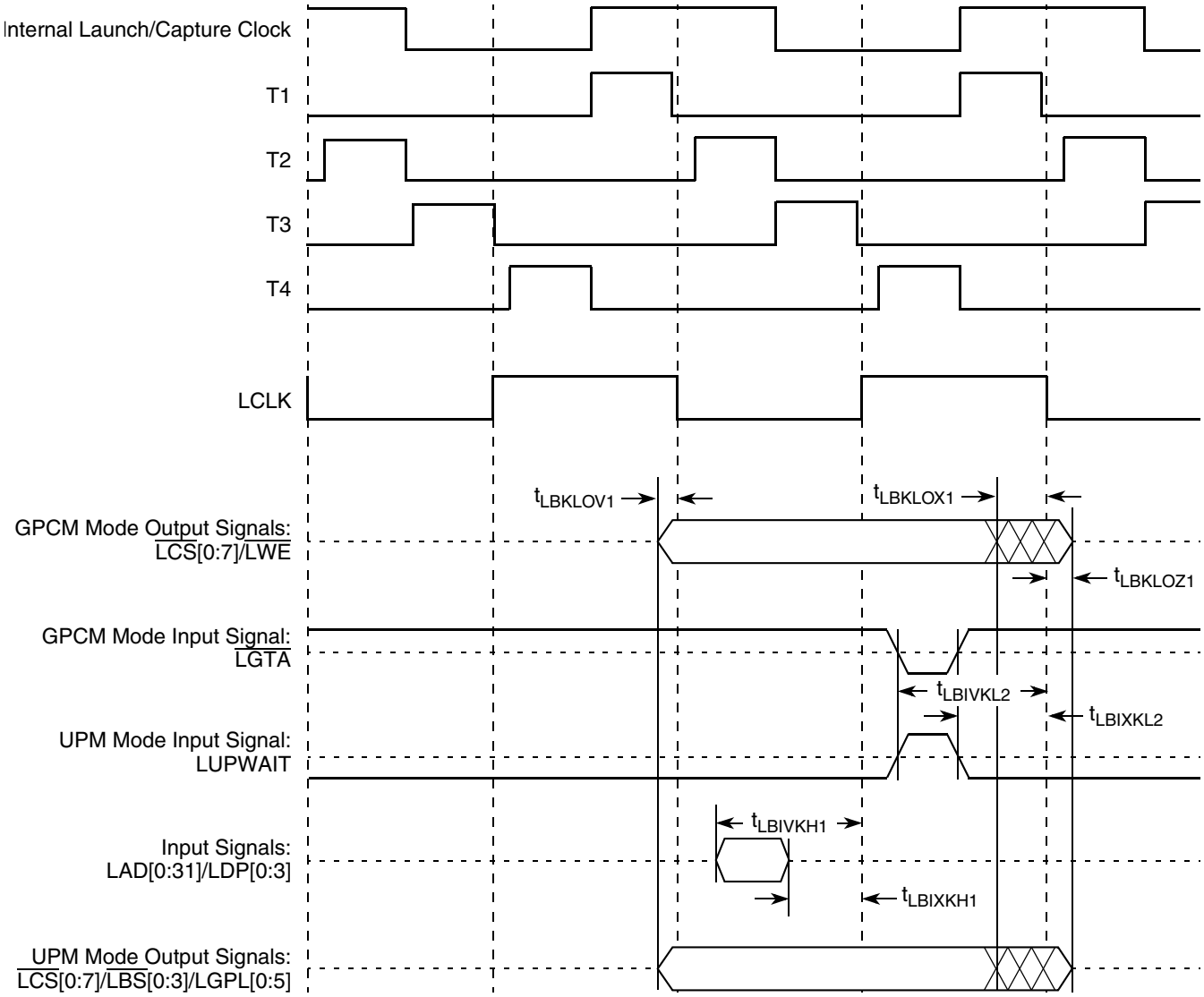

Figure 33. Local Bus Signals, GPCM/UPM Signals for LCCR[CLKDIV] = 8 or 16 (PLL Bypass Mode)

11 Programmable Interrupt Controller

In IRQ edge trigger mode, when an external interrupt signal is asserted (according to the programmed polarity), it must remain the assertion for at least 3 system clocks (SYSCLK periods).

12 JTAG

This section describes the AC electrical specifications for the IEEE 1149.1 (JTAG) interface of the MPC8544E.

12.1 JTAG DC Electrical Characteristics

Table 49 provides the DC electrical characteristics for the JTAG interface.

Table 49. JTAG DC Electrical Characteristics

Parameter	Symbol	Min	Max	Unit	Notes
High-level input voltage	V_{IH}	2	OV_{DD} + 0.3	V	—
Low-level input voltage	V_{IL}	–0.3	0.8	V	—
Input current (OV_{IN} = 0 V or OV_{IN} = OV_{DD})	I_{IN}	—	±5	μA	1
High-level output voltage (OV_{DD} = min, I_{OH} = –2 mA)	V_{OH}	2.4	—	V	—
Low-level output voltage (OV_{DD} = min, I_{OL} = 2 mA)	V_{OL}	—	0.4	V	—

Note:
1. Note that the symbol V_{IN}, in this case, represents the OV_{IN}.

12.2 JTAG AC Electrical Specifications

Table 50 provides the JTAG AC timing specifications as defined in Figure 34 through Figure 37.

Table 50. JTAG AC Timing Specifications (Independent of SYSCLK)[1]

At recommended operating conditions (see Table 3).

Parameter	Symbol[2]	Min	Max	Unit	Notes
JTAG external clock frequency of operation	f_{JTG}	0	33.3	MHz	—
JTAG external clock cycle time	t_{JTG}	30	—	ns	—
JTAG external clock pulse width measured at 1.4 V	t_{JTKHKL}	15	—	ns	—
JTAG external clock rise and fall times	t_{JTGR} & t_{JTGF}	0	2	ns	—
$\overline{\text{TRST}}$ assert time	t_{TRST}	25	—	ns	3
Input setup times: Boundary-scan data TMS, TDI	 t_{JTDVKH} t_{JTIVKH}	 4 0	 — —	ns	4
Input hold times: Boundary-scan data TMS, TDI	 t_{JTDXKH} t_{JTIXKH}	 20 25	 — —	ns	4
Valid times: Boundary-scan data TDO	 t_{JTKLDV} t_{JTKLOV}	 4 4	 20 25	ns	5
Output hold times: Boundary-scan data TDO	 t_{JTKLDX} t_{JTKLOX}	 2.5 4	 — —	ns	5

— For **external DC-coupled** connection, as described in Section 16.2.1, "SerDes Reference Clock Receiver Characteristics," the maximum average current requirements sets the requirement for average voltage (common mode voltage) to be between 100 and 400 mV. Figure 46 shows the SerDes reference clock input requirement for DC-coupled connection scheme.

— For **external AC-coupled** connection, there is no common mode voltage requirement for the clock driver. Since the external AC-coupling capacitor blocks the DC level, the clock driver and the SerDes reference clock receiver operate in different command mode voltages. The SerDes reference clock receiver in this connection scheme has its common mode voltage set to SGND_SRDS*n*. Each signal wire of the differential inputs is allowed to swing below and above the command mode voltage (SGND_SRDS*n*). Figure 47 shows the SerDes reference clock input requirement for AC-coupled connection scheme.

- **Single-ended Mode**
  — The reference clock can also be single-ended. The SD*n*_REF_CLK input amplitude (single-ended swing) must be between 400 and 800 mV peak-peak (from Vmin to Vmax) with $\overline{\text{SD}n\text{\_REF\_CLK}}$ either left unconnected or tied to ground.
  — The SD*n*_REF_CLK input average voltage must be between 200 and 400 mV. Figure 48 shows the SerDes reference clock input requirement for single-ended signaling mode.
  — To meet the input amplitude requirement, the reference clock inputs might need to be DC or AC-coupled externally. For the best noise performance, the reference of the clock could be DC or AC-coupled into the unused phase ($\overline{\text{SD}n\text{\_REF\_CLK}}$) through the same source impedance as the clock input (SD*n*_REF_CLK) in use.

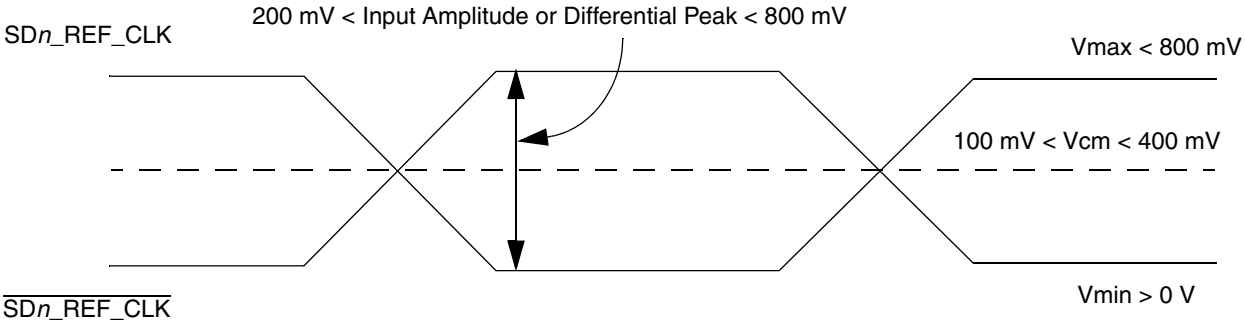

Figure 46. Differential Reference Clock Input DC Requirements (External DC-Coupled)

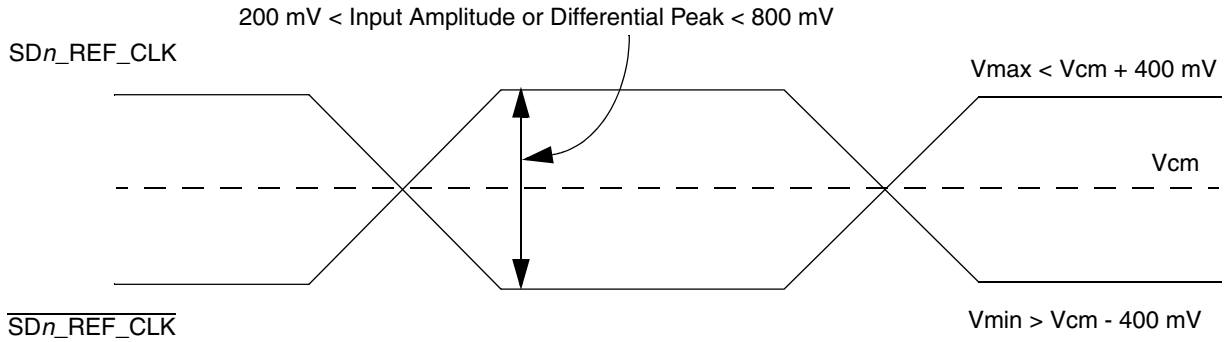

Figure 47. Differential Reference Clock Input DC Requirements (External AC-Coupled)

assumes that the LVPECL clock driver's output impedance is 50 Ω. R1 is used to DC-bias the LVPECL outputs prior to AC-coupling. Its value could be ranged from 140 to 240 Ω depending on clock driver vendor's requirement. R2 is used together with the SerDes reference clock receiver's 50-Ω termination resistor to attenuate the LVPECL output's differential peak level such that it meets the MPC8544E SerDes reference clock's differential input amplitude requirement (between 200 and 800 mV differential peak). For example, if the LVPECL output's differential peak is 900 mV and the desired SerDes reference clock input amplitude is selected as 600 mV, the attenuation factor is 0.67, which requires R2 = 25 Ω. Please consult clock driver chip manufacturer to verify whether this connection scheme is compatible with a particular clock driver chip.

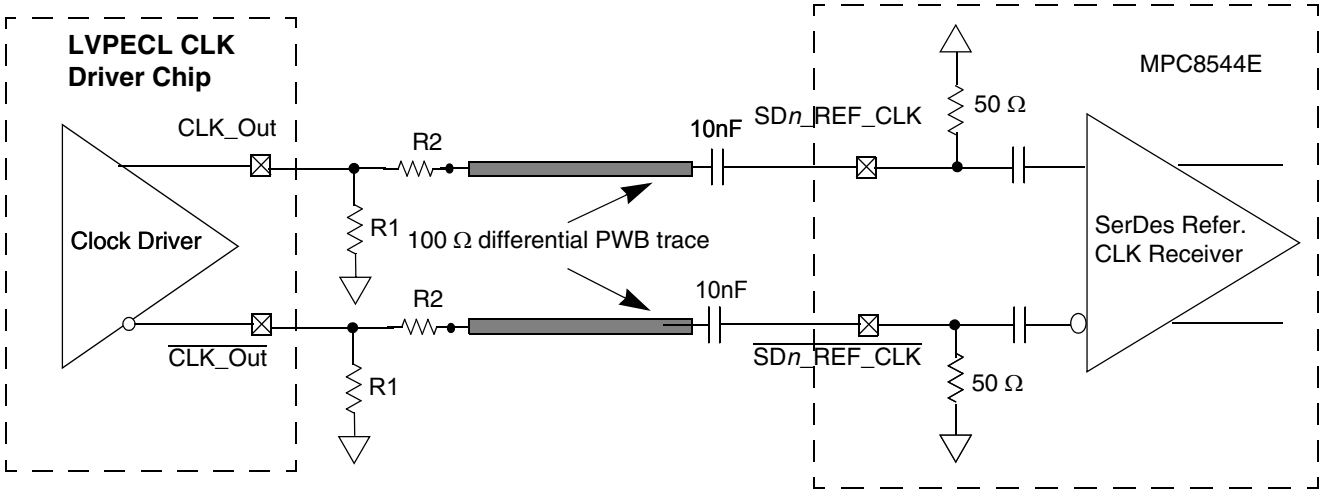

Figure 51. AC-Coupled Differential Connection with LVPECL Clock Driver (Reference Only)

Figure 52 shows the SerDes reference clock connection reference circuits for a single-ended clock driver. It assumes the DC levels of the clock driver are compatible with MPC8544E SerDes reference clock input's DC requirement.

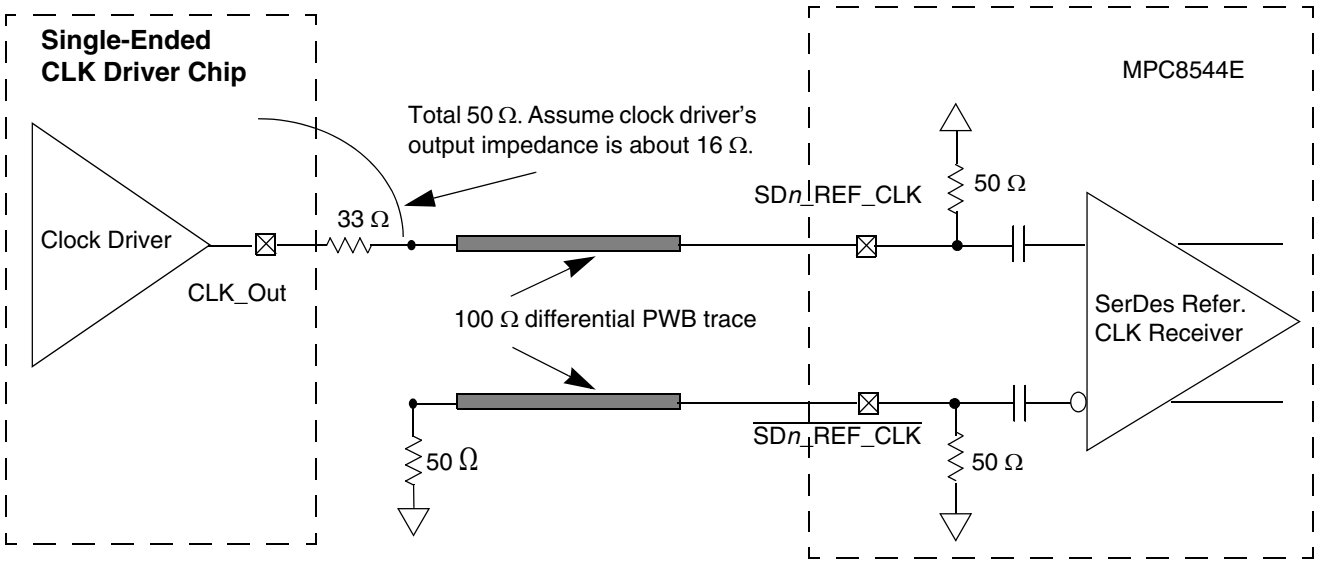

Figure 52. Single-Ended Connection (Reference Only)

16.2.4 AC Requirements for SerDes Reference Clocks

The clock driver selected should provide a high quality reference clock with low phase noise and cycle-to-cycle jitter. Phase noise less than 100 kHz can be tracked by the PLL and data recovery loops and is less of a problem. Phase noise above 15 MHz is filtered by the PLL. The most problematic phase noise occurs in the 1–15 MHz range. The source impedance of the clock driver should be 50 Ω to match the transmission line and reduce reflections which are a source of noise to the system.

Table 57 describes some AC parameters common to SGMII, and PCI Express protocols.

Table 57. SerDes Reference Clock Common AC Parameters

Parameter	Symbol	Min	Max	Unit	Notes
Rising Edge Rate	Rise Edge Rate	1.0	4.0	V/ns	2, 3
Falling Edge Rate	Fall Edge Rate	1.0	4.0	V/ns	2, 3
Differential Input High Voltage	V_{IH}	+200	—	mV	2
Differential Input Low Voltage	V_{IL}	—	–200	mV	2
Rising edge rate (SD*n*_REF_CLK) to falling edge rate ($\overline{\text{SD}n\text{\_REF\_CLK}}$) matching	Rise-Fall Matching	—	20	%	1, 4

Notes:
1. Measurement taken from single ended waveform.
2. Measurement taken from differential waveform.
3. Measured from –200 mV to +200 mV on the differential waveform (derived from SD*n*_REF_CLK minus $\overline{\text{SD}n\text{\_REF\_CLK}}$). The signal must be monotonic through the measurement region for rise and fall time. The 400 mV measurement window is centered on the differential zero crossing. See Figure 53.
4. Matching applies to rising edge rate for SD*n*_REF_CLK and falling edge rate for $\overline{\text{SD}n\text{\_REF\_CLK}}$. It is measured using a 200 mV window centered on the median cross point where SD*n*_REF_CLK rising meets $\overline{\text{SD}n\text{\_REF\_CLK}}$ falling. The median cross point is used to calculate the voltage thresholds the oscilloscope is to use for the edge rate calculations. The rise edge rate of SD*n*_REF_CLK should be compared to the fall edge rate of $\overline{\text{SD}n\text{\_REF\_CLK}}$, the maximum allowed difference should not exceed 20% of the slowest edge rate. See Figure 54.

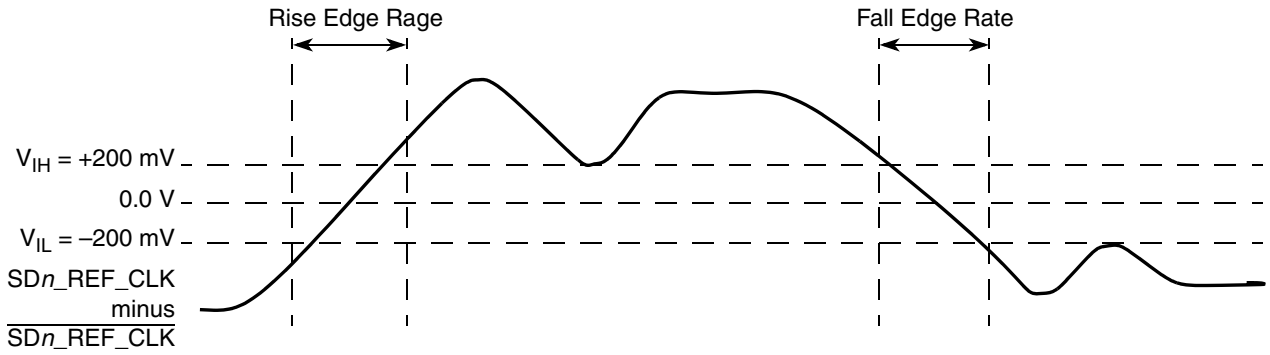

Figure 53. Differential Measurement Points for Rise and Fall Time

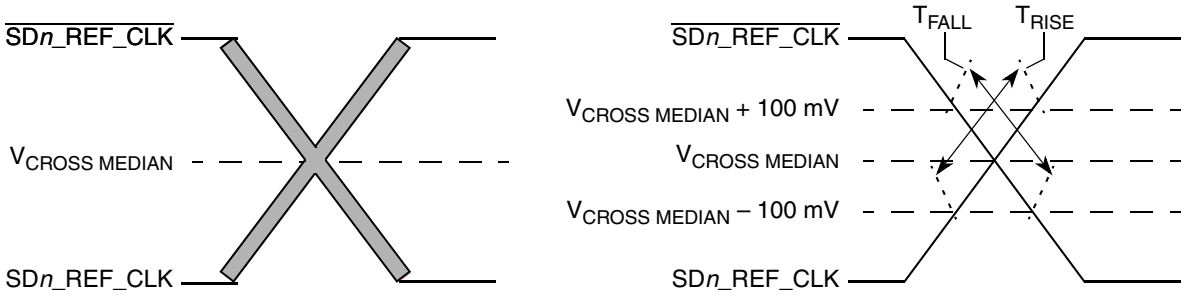

Figure 54. Single-Ended Measurement Points for Rise and Fall Time Matching

The other detailed AC requirements of the SerDes reference clocks is defined by each interface protocol based on application usage. Refer to the following sections for detailed information:

- Section 8.3.1, "The $\overline{\text{DBWO}}$ Signal"
- Section 17.2, "AC Requirements for PCI Express SerDes Clocks"

16.2.4.1 Spread Spectrum Clock

SD1_REF_CLK/$\overline{\text{SD1\_REF\_CLK}}$ were designed to work with a spread spectrum clock (+0 to –0.5% spreading at 30–33 kHz rate is allowed), assuming both ends have same reference clock. For better results, a source without significant unintended modulation should be used.

SD2_REF_CLK/$\overline{\text{SD2\_REF\_CLK}}$ are not intended to be used with, and should not be clocked by, a spread spectrum clock source.

16.3 SerDes Transmitter and Receiver Reference Circuits

Figure 55 shows the reference circuits for SerDes data lane's transmitter and receiver.

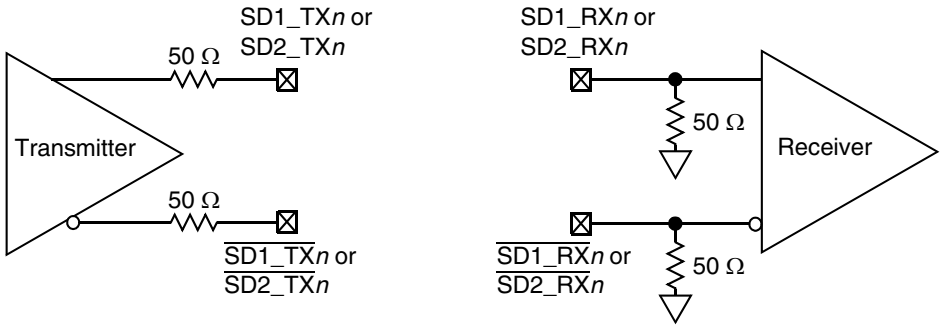

Figure 55. SerDes Transmitter and Receiver Reference Circuits

The DC and AC specification of SerDes data lanes are defined in the section below (PCI Express or SGMII) in this document based on the application usage:

- Section 8.3, "SGMII Interface Electrical Characteristics"
- Section 17, "PCI Express"

Please note that external AC Coupling capacitor is required for the above serial transmission protocols with the capacitor value defined in specification of each protocol section.

17.4.1 Differential Transmitter (TX) Output

Table 59 defines the specifications for the differential output at all transmitters. The parameters are specified at the component pins.

Table 59. Differential Transmitter (TX) Output Specifications

Symbol	Parameter	Min	Nom	Max	Unit	Comments
UI	Unit interval	399.88	400	400.12	ps	Each UI is 400 ps ± 300 ppm. UI does not account for Spread Spectrum Clock dictated variations. See Note 1.
$V_{TX-DIFFp-p}$	Differential peak-to-peak output voltage	0.8	—	1.2	V	$V_{TX-DIFFp-p} = 2*\|V_{TX-D+} - V_{TX-D-}\|$. See Note 2.
$V_{TX-DE-RATIO}$	De- emphasized differential output voltage (ratio)	–3.0	–3.5	–4.0	dB	Ratio of the $V_{TX-DIFFp-p}$ of the second and following bits after a transition divided by the $V_{TX-DIFFp-p}$ of the first bit after a transition. See Note 2.
T_{TX-EYE}	Minimum TX eye width	0.70	—	—	UI	The maximum transmitter jitter can be derived as $T_{TX-MAX-JITTER} = 1 - T_{TX-EYE} = 0.3$ UI. See Notes 2 and 3.
$T_{TX-EYE-MEDIAN-to-MAX-JITTER}$	Maximum time between the jitter median and maximum deviation from the median.	—	—	0.15	UI	Jitter is defined as the measurement variation of the crossing points ($V_{TX-DIFFp-p} = 0$ V) in relation to a recovered TX UI. A recovered TX UI is calculated over 3500 consecutive unit intervals of sample data. Jitter is measured using all edges of the 250 consecutive UI in the center of the 3500 UI used for calculating the TX UI. See Notes 2 and 3.
$T_{TX-RISE}$, $T_{TX-FALL}$	D+/D– TX output rise/fall time	0.125	—	—	UI	See Notes 2 and 5.
$V_{TX-CM-ACp}$	RMS AC peak common mode output voltage	—	—	20	mV	$V_{TX-CM-ACp} = RMS(\|V_{TXD+} - V_{TXD-}\|/2 - V_{TX-CM-DC})$ $V_{TX-CM-DC} = DC_{(avg)}$ of $\|V_{TX-D+} - V_{TX-D-}\|/2$ See Note 2.
$V_{TX-CM-DC-ACTIVE-IDLE-DELTA}$	Absolute delta of DC common mode voltage during LO and electrical idle	0	—	100	mV	$\|V_{TX-CM-DC\ (during\ LO)} - V_{TX-CM-Idle-DC\ (During\ Electrical\ Idle)}\| <= 100$ mV $V_{TX-CM-DC} = DC_{(avg)}$ of $\|V_{TX-D+} - V_{TX-D-}\|/2$ [LO] $V_{TX-CM-Idle-DC} = DC_{(avg)}$ of $\|V_{TX-D+} - V_{TX-D-}\|/2$ [Electrical Idle] See Note 2.
$V_{TX-CM-DC-LINE-DELTA}$	Absolute delta of DC common mode between D+ and D–	0	—	25	mV	$\|V_{TX-CM-DC-D+} - V_{TX-CM-DC-D-}\| <= 25$ mV $V_{TX-CM-DC-D+} = DC_{(avg)}$ of $\|V_{TX-D+}\|$ $V_{TX-CM-DC-D-} = DC_{(avg)}$ of $\|V_{TX-D-}\|$ See Note 2.
$V_{TX-IDLE-DIFFp}$	Electrical idle differential peak output voltage	0	—	20	mV	$V_{TX-IDLE-DIFFp} = \|V_{TX-IDLE-D+} - V_{TX-IDLE-D-}\| <= 20$ mV See Note 2.

Table 62. MPC8544E Pinout Listing (continued)

Signal	Package Pin Number	Pin Type	Power Supply	Notes
V_{DD}	L16, L14, M13, M15, M17, N12, N14, N16, N18, P13, P15, P17, R12, R14, R16, R18, T13, T15, T17, U12, U14, U16, U18,	Power for core (1.0 V)	V_{DD}	—
SVDD_SRDS	M27, N25, P28, R24, R26, T24, T27, U25, W24, W26, Y24, Y27, AA25, AB28, AD27	Core power for SerDes 1 transceivers (1.0 V)	SV_{DD}	—
SVDD_SRDS2	AB1, AC26, AD2, AE26, AG2	Core power for SerDes 2 transceivers (1.0 V)	SV_{DD}	—
XVDD_SRDS	M21, N23, P20, R22, T20, U23, V21, W22, Y20	Pad power for SerDes 1 transceivers (1.0 V)	XV_{DD}	—
XVDD_SRDS2	Y6, AA6, AA23, AF5, AG5	Pad power for SerDes 2 transceivers (1.0 V)	XV_{DD}	—
XGND_SRDS	M20, M24, N22, P21, R23, T21, U22, V20, W23, Y21	—	—	—
XGND_SRDS2	Y4, AA4, AA22, AD4, AE4, AH4	—	—	—
SGND_SRDS	M28, N26, P24, P27, R25, T28, U24, U26, V24, W25, Y28, AA24, AA26, AB24, AB27, AC24, AD28	—	—	—
AGND_SRDS	V27	SerDes PLL GND	—	—
SGND_SRDS2	Y2, AA1, AB3, AC2, AC3, AC25, AD3, AD24, AE3, AE1, AE25, AF3, AH2	—	—	—
AGND_SRDS2	AF1	SerDes PLL GND	—	—
AVDD_LBIU	C28	Power for local bus PLL (1.0 V)	—	19
AVDD_PCI1	AH20	Power for PCI PLL (1.0 V)	—	19
AVDD_CORE	AH14	Power for e500 PLL (1.0 V)	—	19
AVDD_PLAT	AH18	Power for CCB PLL (1.0 V)	—	19

19 Clocking

This section describes the PLL configuration of the MPC8544E. Note that the platform clock is identical to the core complex bus (CCB) clock.

19.1 Clock Ranges

Table 63 provides the clocking specifications for the processor cores and Table 64 provides the clocking specifications for the memory bus.

Table 63. Processor Core Clocking Specifications

Characteristic	Maximum Processor Core Frequency								Unit	Notes
	667 MHz		800 MHz		1000 MHz		1067 MHz			
	Min	Max	Min	Max	Min	Max	Min	Max		
e500 core processor frequency	667	667	667	800	667	1000	667	1067	MHz	1, 2

Notes:
1. **Caution:** The CCB to SYSCLK ratio and e500 core to CCB ratio settings must be chosen such that the resulting SYSCLK frequency, e500 (core) frequency, and CCB frequency do not exceed their respective maximum or minimum operating frequencies. Refer to Section 19.2, "CCB/SYSCLK PLL Ratio," and Section 19.3, "e500 Core PLL Ratio," for ratio settings.
2. The minimum e500 core frequency is based on the minimum platform frequency of 333 MHz.

Table 64. Memory Bus Clocking Specifications

Characteristic	Maximum Processor Core Frequency		Unit	Notes
	667, 800, 1000, 1067 MHz			
	Min	Max		
Memory bus clock speed	166	266	MHz	1, 2

Notes:
1. **Caution:** The CCB clock to SYSCLK ratio and e500 core to CCB clock ratio settings must be chosen such that the resulting SYSCLK frequency, e500 (core) frequency, and CCB clock frequency do not exceed their respective maximum or minimum operating frequencies. Refer to Section 19.2, "CCB/SYSCLK PLL Ratio," and Section 19.3, "e500 Core PLL Ratio," for ratio settings.
2. The memory bus speed is half of the DDR/DDR2 data rate, hence, half of the platform clock frequency.

19.2 CCB/SYSCLK PLL Ratio

The CCB clock is the clock that drives the e500 core complex bus (CCB), and is also called the platform clock. The frequency of the CCB is set using the following reset signals (see Table 65):

- SYSCLK input signal
- Binary value on LA[28:31] at power up

20.3 Thermal Management Information

This section provides thermal management information for the flip chip plastic ball grid array (FC-PBGA) package for air-cooled applications. Proper thermal control design is primarily dependent on the system-level design—the heat sink, airflow, and thermal interface material. The MPC8544E implements several features designed to assist with thermal management, including the temperature diode. The temperature diode allows an external device to monitor the die temperature in order to detect excessive temperature conditions and alert the system; see Section 20.3.4, "Temperature Diode," for more information.

The recommended attachment method to the heat sink is illustrated in Figure 61. The heat sink should be attached to the printed-circuit board with the spring force centered over the die. This spring force should not exceed 10 pounds force (45 Newton).

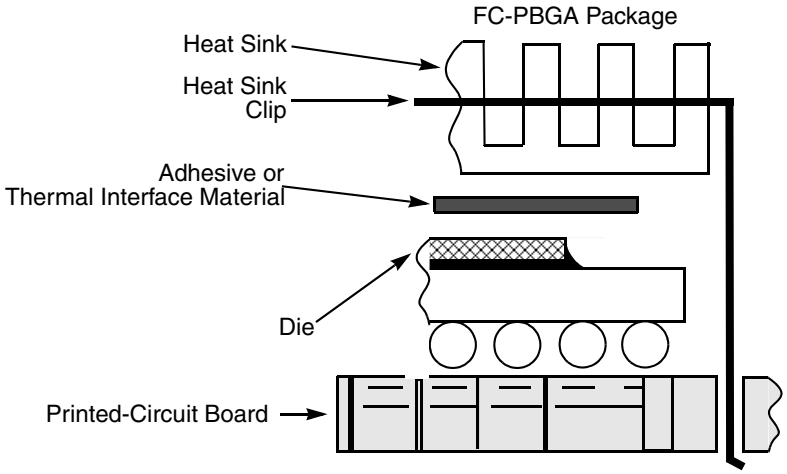

Figure 61. Package Exploded Cross-Sectional View with Several Heat Sink Options

The system board designer can choose between several types of heat sinks to place on the device. There are several commercially-available heat sinks from the following vendors:

Aavid Thermalloy603-224-9988
80 Commercial St.
Concord, NH 03301
Internet: www.aavidthermalloy.com

Advanced Thermal Solutions781-769-2800
89 Access Road #27.
Norwood, MA02062
Internet: www.qats.com

Alpha Novatech408-567-8082
473 Sapena Ct. #12
Santa Clara, CA 95054
Internet: www.alphanovatech.com

Note the following:

- AV_{DD}_SRDS should be a filtered version of SV_{DD}.
- Signals on the SerDes interface are fed from the XV_{DD} power plane.

21.3 Decoupling Recommendations

Due to large address and data buses, and high operating frequencies, the device can generate transient power surges and high frequency noise in its power supply, especially while driving large capacitive loads. This noise must be prevented from reaching other components in the MPC8544E system, and the device itself requires a clean, tightly regulated source of power. Therefore, it is recommended that the system designer place at least one decoupling capacitor at each V_{DD}, TV_{DD}, BV_{DD}, OV_{DD}, GV_{DD}, and LV_{DD} pin of the device. These decoupling capacitors should receive their power from separate V_{DD}, TV_{DD}, BV_{DD}, OV_{DD}, GV_{DD}, and LV_{DD}; and GND power planes in the PCB, utilizing short low impedance traces to minimize inductance. Capacitors may be placed directly under the device using a standard escape pattern. Others may surround the part.

These capacitors should have a value of 0.01 or 0.1 µF. Only ceramic SMT (surface mount technology) capacitors should be used to minimize lead inductance, preferably 0402 or 0603 sizes.

In addition, it is recommended that there be several bulk storage capacitors distributed around the PCB, feeding the V_{DD}, TV_{DD}, BV_{DD}, OV_{DD}, GV_{DD}, and LV_{DD} planes, to enable quick recharging of the smaller chip capacitors. These bulk capacitors should have a low ESR (equivalent series resistance) rating to ensure the quick response time necessary. They should also be connected to the power and ground planes through two vias to minimize inductance. Suggested bulk capacitors—100–330 µF (AVX TPS tantalum or Sanyo OSCON). However, customers should work directly with their power regulator vendor for best values and types and quantity of bulk capacitors.

21.4 SerDes Block Power Supply Decoupling Recommendations

The SerDes block requires a clean, tightly regulated source of power (SV_{DD} and XV_{DD}) to ensure low jitter on transmit and reliable recovery of data in the receiver. An appropriate decoupling scheme is outlined below.

Only surface mount technology (SMT) capacitors should be used to minimize inductance. Connections from all capacitors to power and ground should be done with multiple vias to further reduce inductance.

- First, the board should have at least 10 × 10-nF SMT ceramic chip capacitors as close as possible to the supply balls of the device. Where the board has blind vias, these capacitors should be placed directly below the chip supply and ground connections. Where the board does not have blind vias, these capacitors should be placed in a ring around the device as close to the supply and ground connections as possible.
- Second, there should be a 1-µF ceramic chip capacitor on each side of the device. This should be done for all SerDes supplies.
- Third, between the device and any SerDes voltage regulator there should be a 10-µF, low equivalent series resistance (ESR) SMT tantalum chip capacitor and a 100-µF, low ESR SMT tantalum chip capacitor. This should be done for all SerDes supplies.

22.2 Nomenclature of Parts Fully Addressed by this Document

Table 75 provides the Freescale part numbering nomenclature for the MPC8544E.

Table 75. Device Nomenclature

MPC	*nnnn*	*E*	*C*	*HX*	*AA*	*X*	*B*
Product Code	**Part Identifier**	**Encryption Acceleration**	**Temperature Range**	**Package[1]**	**Processor Frequency[2]**	**Platform Frequency**	**Revision Level**
MPC	8544	Blank = not included E = included	B or Blank = Industrial Tier standard temp range(0° to 105°C) C = Industrial Tier Extended temp range(–40° to 105°C)	VT = FC-PBGA (lead-free) VJ = lead-free FC-PBGA	AL = 667 MHz AN = 800 MHz AQ = 1000 MHz AR = 1067 MHz	F = 333 MHz G = 400 MHz J = 533 MHz	Blank = Rev. 1.1 1.1.1 A = Rev. 2.1

Notes:
1. See Section 18, “Package Description,” for more information on available package types.
2. Processor core frequencies supported by parts addressed by this specification only. Not all parts described in this specification support all core frequencies. Additionally, parts addressed by part number specifications may support other maximum core frequencies.
3. The VT part number is ROHS-compliant, with the permitted exception of the C4 die bumps.
4. The VJ part number is entirely lead-free. This includes the C4 die bumps.

22.3 Part Marking

Parts are marked as in the example shown in Figure 70.

FC-PBGA

Notes:
MMMMM is the 5-digit mask number.
ATWLYYWW is the traceability code.
CCCCC is the country of assembly. This space is left blank if parts are assembled in the United States.

Figure 70. Part Marking for FC-PBGA Device